

ABSTRACT OF THE DISCLOSURE

A semiconductor device of MCM type allowing high-density assembly and a process of fabricating the same is provided.

There are provided semiconductor chips mounted on a supporting substrate and incrustated in an insulation film on the supporting substrate and wiring formed in the insulation film so as to connect to each semiconductor chip through connection holes provided in the insulation film. Then, an interlayer dielectric covers such wiring that is connected to an upper layer wiring, through connection holes provided in such interlayer dielectric.

In addition, an upper layer insulation film covers the upper layer wiring, and an electrode, connected to such upper layer wiring through another connection hole, is provided on such upper layer insulation film.